

Philippe Ferrandis

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Transport properties of a thin GaN channel formed in an Al _{0.9} Ga _{0.1} N/GaN heterostructure grown on AlN/sapphire template. Journal of Applied Physics, 2022, 131, 124501.	1.1	2
2	Investigation of sidewall damage induced by reactive ion etching on AlGaInP MESA for micro-LED application. Journal of Luminescence, 2021, 234, 117937.	1.5	32
3	Characterization and role of deep traps on the radio frequency performances of high resistivity substrates. Journal of Applied Physics, 2021, 129, 215701.	1.1	0
4	Analysis of hole-like traps in deep level transient spectroscopy spectra of AlGaIn/GaN heterojunctions. Journal Physics D: Applied Physics, 2020, 53, 185105.	1.3	2
5	Characterization of micro-pixelated InGaP/AlGaInP quantum well structures. , 2020, , .		2
6	Study of deep traps in AlGaIn/GaN high-electron mobility transistors by electrical characterization and simulation. Journal of Applied Physics, 2019, 125, .	1.1	9
7	Deep traps localization in AlGaIn/GaN MIS-HEMTs by a comparative study using capacitance and current deep level transient spectroscopies. Journal of Physics: Conference Series, 2019, 1190, 012013.	0.3	1
8	Gate length effect on trapping properties in AlGaIn/GaN high-electron-mobility transistors. Semiconductor Science and Technology, 2019, 34, 045011.	1.0	4
9	Electrical properties of thin silicon oxides grown at room temperature by ion beam sputtering technique. Journal of Materials Science: Materials in Electronics, 2019, 30, 4880-4884.	1.1	0
10	Electrical properties of metal/Al ₂ O ₃ /In _{0.53} Ga _{0.47} As capacitors grown on InP. Journal of Applied Physics, 2018, 123, 161534.	1.1	8
11	AlGaIn/GaN metal-insulator-semiconductor capacitors with a buried Mg doped layer characterized by deep level transient spectroscopy and photoluminescence. , 2018, , .		3
12	Effects of negative bias stress on trapping properties of AlGaIn/GaN Schottky barrier diodes. Microelectronic Engineering, 2017, 178, 158-163.	1.1	11
13	Ion-assisted gate recess process induced damage in GaN channel of AlGaIn/GaN Schottky barrier diodes studied by deep level transient spectroscopy. Japanese Journal of Applied Physics, 2017, 56, 04CG01.	0.8	12
14	Deep-level transient spectroscopy of interfacial states in "buffer-free" p-i-n GaSb/GaAs devices. Journal of Applied Physics, 2013, 114, 134507.	1.1	12
15	Ferroelectric Bi _{3.25} La _{0.75} Ti ₃ O ₁₂ thin films on a conductive Sr ₄ Ru ₂ O ₉ electrode obtained by pulsed laser deposition. Thin Solid Films, 2007, 515, 6314-6318.	0.8	4
16	Influence of an epitaxial Si capping of Ge islands on Si(0 0 1) and Si(1 1 0) by LPCVD. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 507-509.	1.3	1
17	Growth and characterization of Ge islands on Si(110). Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 89, 171-175.	1.7	9
18	Optical characterisation of Ge islands grown on Si(110). Microelectronics Journal, 2002, 33, 541-546.	1.1	2